



Frontier Electronics Corp.

667 E. COCHRAN STREET, SIMI VALLEY, CA 93065
 TEL: (805) 522-9998 FAX: (805) 522-9989
 E-mail: frontiersales@frontierusa.com
 Web: <http://www.frontierusa.com>

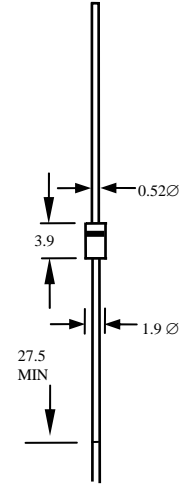
SILICON EPITAXIAL PLANAR DIODE **BAV21**

FEATURES

- FAST SWITCHING
- SMALL SIZE

MECHANICAL DATA

- CASE: GLASS, DO35, DIMENSIONS IN MILLIMETERS
- LEADS: SOLDERABLE PER MIL-STD-202, METHOD 208
- POLARITY: CATHODE INDICATED BY COLOR BAND
- WEIGHT: 0.13 GRAMS



RATINGS	SYMBOL	BAV21	UNITS
REVERSE VOLTAGE	V_R	250	V
RECTIFIED CURRENT (AVERAGE) HALF WAVE RECTIFICATION WITH RESIST LOAD AT $T_{amb} = 25^{\circ}\text{C}$ AND $\geq 50\text{HZ}$ (NOTE 1)	I_O	200	mA
SURGE FORWARD CURRENT AT $T < 1\text{ s}$ AND $T_J = 25^{\circ}\text{C}$	I_{FSM}	1	A
POWER DISSIPATION AT $T_{amb}=25^{\circ}\text{C}$ (NOTE 1)	P_{TOT}	400	mW
JUNCTION TEMPERATURE	T_J	175	$^{\circ}\text{C}$
STORAGE TEMPERATURE RANGE	T_S	- 55 TO + 175	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS (AT $T_A = 25^{\circ}\text{C}$ UNLESS OTHERWISE NOTED)

CHARACTERISTICS	SYMBOL	MAX	UNITS
FORWARD VOLTAGE AT $I_F=100\text{mA}$	V_F	1	V
LEAKAGE CURRENT AT $V_R=200\text{V}$	I_R	100	nA
AT $V_R=200\text{V}$ $T_J=100^{\circ}\text{C}$	I_R	15	μA
CAPACITANCE AT $V_F=V_R=0$	C_{TOT}	1.5	PF
REVERSE RECOVERY TIME FROM $I_F=30\text{mA}$ THROUGH $I_R=30\text{mA}$ TO $I_R=3\text{mA}$; $R_L=100\Omega$	T_{RR}	50	nS
THERMAL RESISTANCE JUNCTION TO AMBIENT AIR (NOTE 1)	R_{THA}	0.375	K / mW

NOTE: 1. LEADS KEPT AT AMBIENT TEMP. AT 8mm LENGTH

RATINGS AND CHARACTERISTIC CURVE BAV21

FIG. 1-FORWARD CHARACTERISTIC

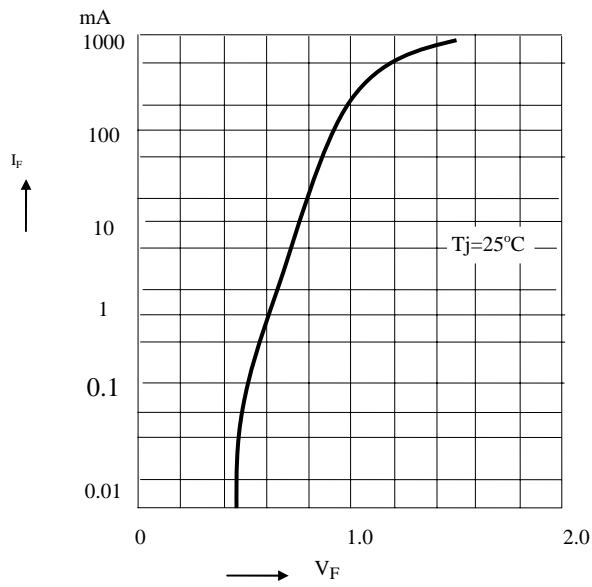


FIG. 2-LEAKAGE CURRENT VERSUS JUNCTION TEMPERATURE

